

This listing of claims replaces all prior versions, and listings, of claims in this application.

Listing of Claims:

1-7. (Canceled)

8. (Currently Amended) A method of forming a lightly doped drain, ~~said lightly doped drain is formed~~ in a thin film transistor, comprising:

- providing a glass substrate and a polysilicon structure on said glass substrate;
- depositing an insulating layer on said polysilicon structure and said glass substrate;
- depositing a metal layer on said insulating layer;
- forming a photo resist layer, having a transferred, pattern on said metal layer;
- dry etching a portion of said metal layer to expose a portion of said insulating layer, ~~said step of dry etching uses~~ using said photo resist layer as a first mask;
- implanting multiple (M) first ions through said insulating layer into said polysilicon structure, ~~said step of implanting uses~~ using said photo resist layer and said metal layer as a second mask;
- isotropic etching a portion of said metal layer such that undercut of said metal layer under said photo resist layer is observed;
- removing said photo resist layer; and
- implanting multiple (M) second ions into said polysilicon structure to form said lightly doped drain, ~~said step of implanting uses~~ using said undercut metal layer as a third mask.

9. (Original) A method according to claim 8, wherein the step of isotropic etching comprises wet etching a portion of said metal layer.

10. (Canceled)

11. (Currently Amended) A method of forming a lightly doped drain, said lightly doped drain is formed in a thin film transistor, comprising:

providing a glass substrate and a polysilicon structure on said glass substrate;

depositing an insulating layer on said polysilicon structure and said glass substrate;

depositing a metal layer on said insulating layer;

forming a photo resist layer, having a transferred, pattern on said metal layer;

dry etching a portion of said metal layer to expose a portion of said insulating layer, ~~said step of dry etching uses~~ using said photo resist layer as a first mask;

implanting multiple (M) first ions through said insulating layer into said polysilicon structure, ~~said step of implanting uses~~ using said photo resist layer and said metal layer as a second mask;

isotropic etching a portion of said metal layer such that undercut of said metal layer under said photo resist layer is observed, said step of isotropic etching including a step of wet etching;

removing said photo resist layer; and

implanting multiple (M) second ions into said polysilicon structure to form said lightly doped drain, ~~said step of implanting uses~~ using said undercut metal layer as a third mask.